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(54) **Title:** SEMICONDUCTOR DEVICE HAVING BACKSIDE REDISTRIBUTION LAYERS AND METHOD FOR FABRICATING THE SAME

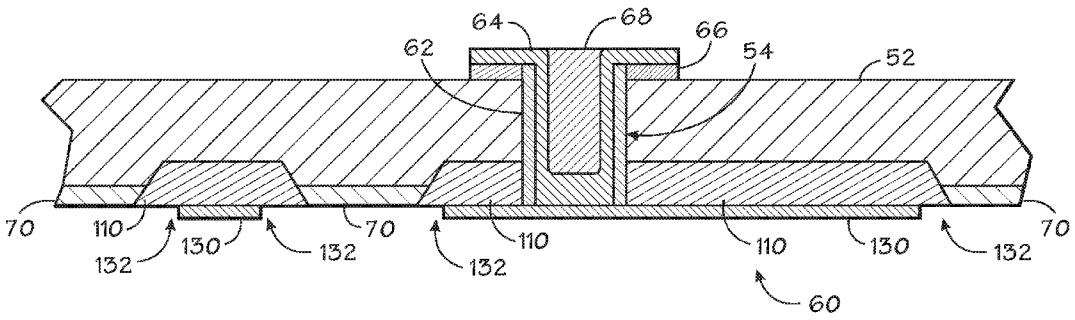


FIG. 11

(57) **Abstract:** Present embodiments relate to a semiconductor device having a backside redistribution layer and a method for forming such a layer. Specifically, one embodiment includes providing a substrate comprising a via (54) formed therein. The substrate has a front side and a backside. The embodiment may further include forming a trench on the backside of the substrate, disposing an insulating material (110) in the trench, and forming a trace (130) over the insulating material in the trench.

WO 2009/017923 A1